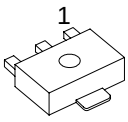
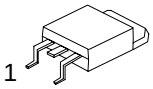
2SB1260

PNP SILICON TRANSISTOR

POWER TRANSISTOR



SOT-89



TO-252

*Pb-free plating product number: 2SB1260L

■ DESCRIPTION

The UTC 2SB1260 is a epitaxial planar type PNP silicon transistor.

■ FEATURES

*High breakdown voltage and high current.
BV_{CEO}= -80V, I_C= -1A
*Good h_{FE} linearity.
*Low $V_{CE(SAT)}$

■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2SB1260-x-AB3-R	2SB1260L-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SB1260-x-TN3-R	2SB1260L-x-TN3-R	TO-252	B	C	E	Tape Reel
2SB1260-x-TN3-T	2SB1260L-x-TN3-T	TO-252	B	C	E	Tube

2SB1260L-x-AB3-R

(1)Packing Type	(1) B: Tape Box, K: Bulk, R: Tape Reel
(2)Package Type	(2) AB3: SOT-89, TN3: TO-252
(3)Rank	(3) refer to Classification of h_{FE}
(4)Lead Plating	(4) L: Lead Free Plating, Blank: Pb/Sn

■ ABSOLUATE MAXIUM RATINGS (Ta = 25℃)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector -Base Voltage		V_{CBO}	-80	V
Collector -Emitter Voltage		V_{CEO}	-80	V
Emitter -Base Voltage		V_{EBO}	-5	V
Peak Collector Current (single pulse, Pw=100ms)		I_{CM}	-2	A
DC Collector Current		I_C	-1	A
Power Dissipation	SOT-89	P_D	0.5	W
	TO-252		1.9	W
Operating Temperature		T_J	+150	℃
Storage Temperature		T_{STG}	-40 ~ +150	℃

Note 1. Printed circuit board,1.7mm thick, collector copper plating 100mm^2 or larger.

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25℃, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV_{CBO}	I_C= -50μA	-80			V
Collector Emitter Breakdown Voltage	BV_{CEO}	I_C= -1mA	-80			V
Emitter Base Breakdown Voltage	BV_{EBO}	I_E= -50μA	-5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-60V			-1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-4V			-1	μA
DC Current Gain(Note 1)	h_{FE}	V_{CE}=-3V, I_{OUT}=-0.1A	82		390	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=-500mA, I_B=-50mA			-0.4	V
Transition Frequency	f_T	V_{CE}= -5V, I_E=50mA, f=30MHz		100		MHz
Output Capacitance	Cob	V_{CB}=-10V, I_E=0, f=1MHz		25		pF

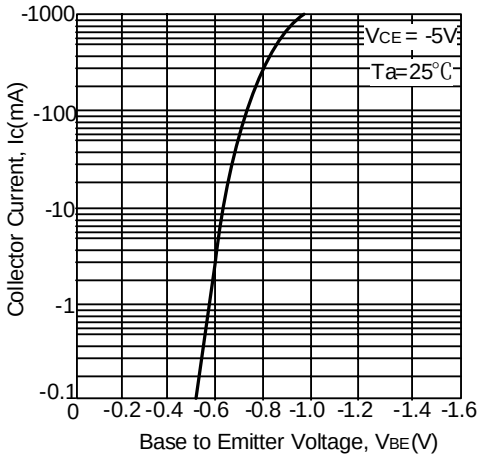
Note 1: Pulse test: P_W<300μs, Duty Cycle<2%

■ CLASSIFICATION OF h_{FE}

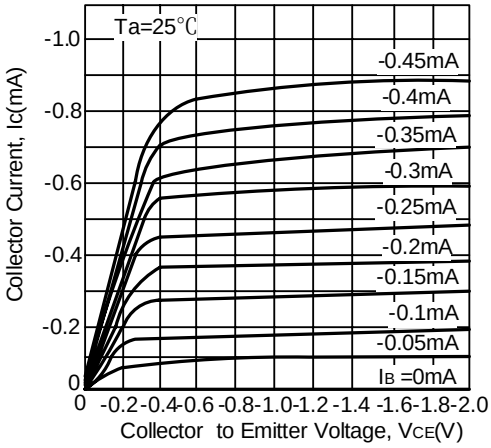
RANK	P	Q	R
RANGE	82 ~ 180	120 ~ 270	180 ~ 390

■ TYPICAL CHARACTERICS

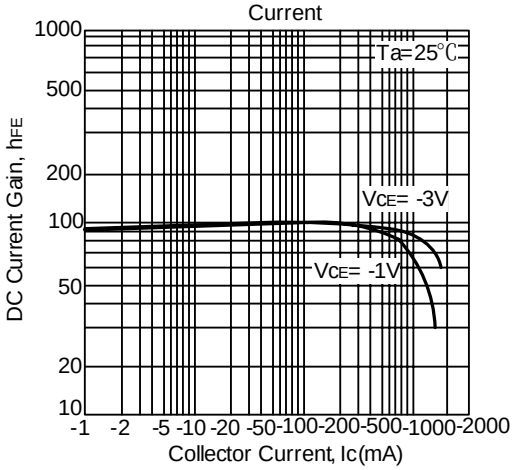
Grounded Emitter Propagation Characteristics



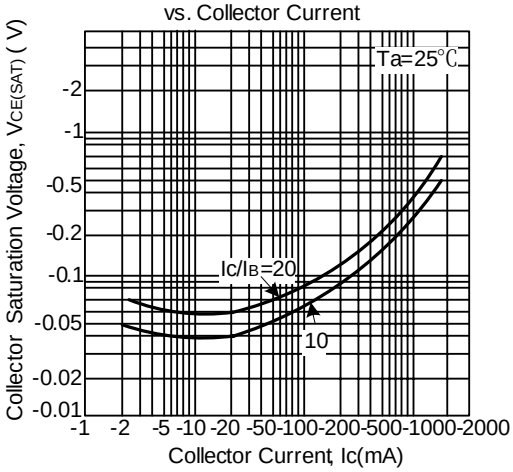
Grounded Emitter Output Characteristics



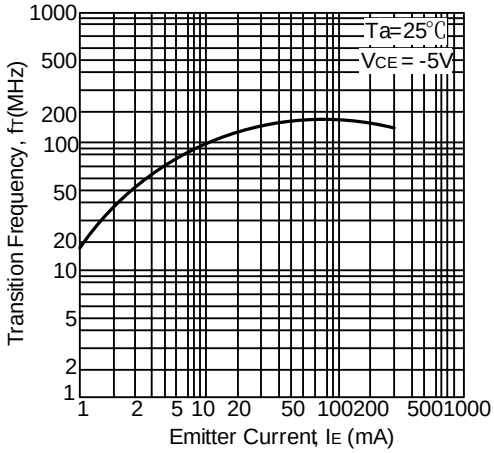
DC Current Gain vs. Collector Current



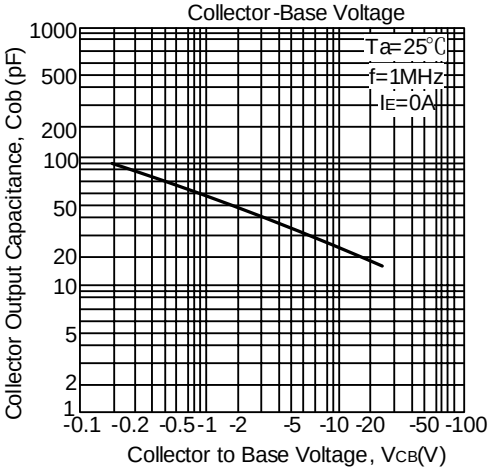
Collector-emitter Saturation Voltage vs. Collector Current



Gain Bandwidth Product vs. Emitter Current



Collector Output Capacitance vs. Collector-Base Voltage



■ TYPICAL CHARACTERICS(Cont.)